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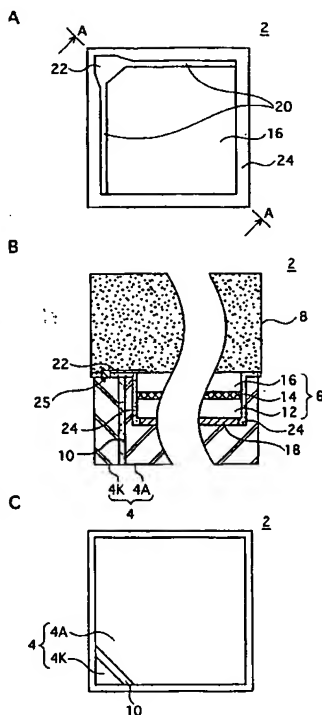
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(54) Title: SEMICONDUCTOR LIGHT EMITTING DEVICE, LIGHTING MODULE, LIGHTING APPARATUS, AND MANU-
FACTURING METHOD OF SEMICONDUCTOR LIGHT EMITTING DEVICE



(57) Abstract: An LED bare chip which is one type of a semiconductor light emitting device (2) includes a multilayer epitaxial structure (6) composed of a p-GaN layer (12), an InGaN/GaN MQW light emitting layer (14) and an n-GaN layer (16). A p-electrode (18) is formed on the p-GaN layer (12), and an n-electrode (20) is formed on the n-GaN layer (16). An Au plating layer (4) is formed on the p-electrode (18). The Au plating layer (4) supports the multilayer epitaxial structure (6) and conducts heat generated in the light emitting layer (14). The Au plating layer (4) is electrically divided into two portions by a polyimide member (10). One of the two portions (4A) is connected to the p-electrode (18), to be constituted as an anode power supply terminal, and the other portion (4K) is connected to the n-electrode (20) by a wiring (22), to be constituted as a cathode power supply terminal.

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